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APPLICATION FOR LETTERS PATENT

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DEPOSITION METHODS

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-INVENTORS-

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DEPOSITION METHODS

TECHNICAL FIELD

This invention relates to deposition methods including, but not limited to, atomic layer deposition.

BACKGROUND OF THE INVENTION

Atomic layer deposition (ALD) is recognized as a deposition technique that forms high quality materials with minimal defects and tight statistical process control. Even so, it is equally recognized that ALD can have limited application. In some circumstances, the theoretically expected quality of an ALD layer is not achieved.

It can be seen that a need exists for an ALD method that forms a layer without introducing intolerable defects into the material.

SUMMARY OF THE INVENTION

In accordance with an aspect of the invention, a deposition method includes contacting a substrate with a first initiation precursor and forming a first portion of an initiation layer on the substrate. At least a part of the substrate is contacted with a second initiation precursor different from the first initiation precursor and a second portion of the initiation layer is formed on the substrate. Another aspect of the invention includes simultaneously contacting a substrate with a plurality

1 of initiation precursors, forming on the substrate an initiation layer
2 comprising components derived from each of the plurality of initiation
3 precursors. Also, in another aspect, a deposition method includes
4 contacting a substrate with a first initiation precursor and forming a first
5 initiation layer on the substrate. The first initiation layer is contacted
6 with a deposition precursor and a deposition layer is formed on the first
7 initiation layer. Next, at least the deposition layer is contacted with a
8 second initiation precursor different from the first initiation precursor
9 and a second initiation layer is formed over the substrate. In another
10 aspect, a deposition method includes contacting a first-type surface of a
11 substrate and a second-type surface of a substrate different from the
12 first-type surface with a first initiation precursor and forming an
13 initiation layer substantially selectively on the first-type surface relative
14 to the second-type surface. The initiation layer is contacted with a
15 deposition precursor and a deposition layer is formed substantially
16 selectively over the first-type surface relative to the second-type surface.

17 18 19 **BRIEF DESCRIPTION OF THE DRAWINGS**

20 Preferred embodiments of the invention are described below with
21 reference to the following accompanying drawings.

22 Fig. 1 is an enlarged sectional view of a wafer portion at one
23 processing step in the prior art.

1 Fig. 2 is an enlarged sectional view of a wafer portion at one
2 processing step in accordance with one aspect of the invention.

3 Fig. 3 is an enlarged sectional view of a portion of the Fig. 2
4 wafer at a processing step subsequent to that depicted by Fig. 2.

5 Fig. 4 is an enlarged sectional view of a portion of the Fig. 3
6 wafer at a processing step subsequent to that depicted by Fig. 3.

7 Fig. 5 is an enlarged sectional view of a wafer portion at one
8 processing step in accordance with another aspect of the invention.

9 Fig. 6 is an enlarged sectional view of a portion of the Fig. 5
10 wafer at a processing step subsequent to that depicted by Fig. 5.

11 Fig. 7 is an enlarged sectional view of a wafer portion at one
12 processing step in accordance with another aspect of the invention.

13 Fig. 8 is a top view of a portion of the Fig. 7 wafer.

14 Fig. 9 is an enlarged sectional view of a wafer portion at one
15 processing step in accordance with another aspect of the invention.

16 17 DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

18 This disclosure of the invention is submitted in furtherance of the
19 constitutional purposes of the U.S. Patent Laws "to promote the progress
20 of science and useful arts" (Article 1, Section 8).

21 Atomic layer deposition (ALD) involves formation of successive
22 atomic layers on a substrate. Such layers may comprise an epitaxial,
23 polycrystalline, amorphous, etc. material. ALD may also be referred to

1 as atomic layer epitaxy, atomic layer processing, etc. Further, the
2 invention may encompass other deposition methods not traditionally
3 referred to as ALD, for example, chemical vapor deposition (CVD), but
4 nevertheless including the method steps described herein. The deposition
5 methods herein may be described in the context of formation on a
6 semiconductor wafer. However, the invention encompasses deposition on
7 a variety of substrates besides semiconductor substrates.

8 In the context of this document, the term "semiconductor
9 substrate" or "semiconductive substrate" is defined to mean any
10 construction comprising semiconductive material, including, but not limited
11 to, bulk semiconductive materials such as a semiconductive wafer (either
12 alone or in assemblies comprising other materials thereon), and
13 semiconductive material layers (either alone or in assemblies comprising
14 other materials). The term "substrate" refers to any supporting
15 structure, including, but not limited to, the semiconductive substrates
16 described above.

17 Described in summary, ALD includes exposing an initial substrate
18 to a first chemical specie to accomplish chemisorption of the specie onto
19 the substrate. Theoretically, the chemisorption forms a monolayer that
20 is uniformly one atom or molecule thick on the entire exposed initial
21 substrate. Practically, as further described below, chemisorption might
22 not occur on all portions of the substrate. Nevertheless, such an
23 imperfect monolayer is still a monolayer in the context of this document.

1 The first specie is purged from over the substrate and a second chemical
2 specie is provided to chemisorb onto the first monolayer of the first
3 specie. The second specie is then purged and the steps are repeated
4 with exposure of the second specie monolayer to the first specie. In
5 some cases, the two monolayers may be of the same specie. Also,
6 additional species may be successively chemisorbed and purged just as
7 described for the first and second species.

8 ALD is often described as a self-limiting process, in that a finite
9 number of sites exist on a substrate to which the first specie may form
10 chemical bonds. The second species might only bond to the first specie
11 and thus may also be self-limiting. Once all of the finite number of
12 sites on a substrate are bonded with a first specie, the first specie will
13 often not bond to other of the first specie already bonded with the
14 substrate. However, process conditions can be varied in ALD as
15 discussed below to promote such bonding and render ALD not self-
16 limiting. Accordingly, ALD may also encompass a specie forming other
17 than one monolayer at a time by stacking of a specie, forming a layer
18 more than one atom or molecule thick. The various aspects of the
19 present invention described herein are applicable to any circumstance
20 where ALD may be desired. A few examples of materials that may be
21 deposited by ALD include silicon nitride, zirconium oxide, tantalum
22 oxide, aluminum oxide, and others.

1 ALD offers a variety of advantages and improvements over other
2 methods of forming materials on a substrate. However, ALD layers
3 formed on a substrate may also possess thickness variations caused by
4 variations in the composition and/or surface properties of the underlying
5 substrate. Such disadvantage can limit the application of ALD methods
6 to exclude applications where ALD might otherwise be particularly
7 advantageous.

8 For example, when a material is to be deposited simultaneously
9 over multiple types of substrates or over a single type of substrate
10 having different surface properties, ALD may be a poor candidate for
11 forming the material. Experience indicates that material formed by ALD
12 may not form at a uniform rate on differing types of substrates or on
13 a single type of substrate having multiple surface properties in multiple
14 areas. The different rates of formation produce defects and/or varying
15 thicknesses in the deposited material. Accordingly, even though ALD
16 may be used to form very thin layers of material, thickness variations
17 may produce unacceptable defects.

18 A deposition method according to one aspect of the invention
19 comprises contacting a substrate with a first initiation precursor and
20 forming a first portion of an initiation layer on the substrate. A wafer
21 portion 2 is shown in Fig. 1, including a substrate 4. As indicated
22 above, substrate 4 may comprise a variety of materials, including a
23 semiconductive, conductive, insulative, or other material. A layer of a

1 first initiation precursor 6 is formed on an outer surface of substrate 4
2 as a first portion of an initiation layer. The initiation layer may not be
3 formed uniformly across substrate 4, as shown. Substrate 4 is exposed
4 through an opening in the initiation layer. One problem among
5 conventional deposition methods is that such openings in an initiation
6 layer can result in defects or unevenness as successive layers are formed
7 on the initiation layer.

8 Failure of the first initiation precursor 6 to form an initiation layer
9 in certain regions may be caused by a variety of circumstances. For
10 example, the amenability of a particular initiation precursor to form an
11 initiation layer may depend on the type of substrate. Also, for example,
12 even when the material from which a substrate is formed is substantially
13 homogeneous, differences may exist in the type of surface provided with
14 relation to the deposition method. Crystalline or other defects in a
15 surface of a substrate may prevent a particular initiation precursor from
16 forming an initiation layer uniformly across the substrate surface. It is
17 further contemplated that yet other circumstances may prevent the
18 formation of a uniform initiation layer on substrate 4.

19 Accordingly, in one aspect of the present invention, at least a part
20 of substrate 4 is contacted with a second initiation precursor different
21 from the first initiation precursor, forming a second portion of the
22 initiation layer on substrate 4. Fig. 2 shows wafer portion 2 wherein a
23 second initiation precursor 8 forms a second portion of the initiation

1 layer on the substrate. The second portion fills the opening in the first
2 portion of the initiation layer where first initiation precursor 6 failed to
3 form an initiation layer. The contacting of substrate 4 with first
4 initiation precursor 6 and second initiation precursor 8 may occur
5 separately or simultaneously. When contacting occurs separately, the
6 initiation layer may form in two different portions, the second portion
7 filling openings in the first portion. When contacting occurs
8 simultaneously, the first and second portions of the initiation layer may
9 also be formed simultaneously.

10 It is conceivable that two or more initiation precursors may be
11 desired to form an initiation layer having sufficient uniformity.
12 Accordingly, another aspect of the invention involves simultaneously or
13 otherwise contacting substrate 4 with a plurality of initiation precursors
14 and forming on substrate 4 an initiation layer comprising components
15 derived from each of the plurality of initiation precursors. The plurality
16 of initiation precursors could include first initiation precursor 6 and
17 second initiation precursor 8, as well as other initiation precursors. As
18 described above, a portion of the initiation layer derived from one of
19 the plurality of initiation precursors may form on the substrate in a
20 region less susceptible to formation of the initiation layer by another of
21 the plurality of initiation precursors. Such may be the case where the
22 portion of the initiation layer derived from the one initiation precursor
23 substantially fills pinholes 24 in the initiation layer formed by the

1 another initiation precursor. Pinholes 24 are shown in Fig. 8 and
2 discussed below.

3 One characteristic of CVD is the simultaneous presence of multiple
4 precursors in the deposition chamber that react to form the deposited
5 material. Such condition is contrasted with the purging criteria for
6 traditional ALD where a single deposition precursor is contacted with a
7 substrate and chemisorbs to the substrate or previously deposited
8 precursor. The deposition process regime described herein may provide
9 simultaneously present precursors of a type or under conditions such that
10 chemisorption, rather than CVD reaction occurs. The plurality of
11 initiation precursors do not react together as in CVD. Rather, they
12 chemisorb to the substrate, providing a surface onto which a deposition
13 precursor may next chemisorb to form a complete layer of desired
14 material.

15 As shown in Fig. 3, the deposition method may further comprise
16 contacting the first and second portions of the initiation layer with a
17 deposition precursor 10 and forming a deposition layer on the first and
18 second portions of the initiation layer. Accordingly, a deposition layer
19 is formed on the portion of the initiation layer derived from first
20 initiation precursor 6 and another portion of the initiation layer derived
21 from second initiation precursor 8. A deposition method may
22 additionally include contacting the deposition layer formed from
23 deposition precursor 10 with a third initiation precursor 12 to form a

1 second initiation layer, as shown in Fig. 4. Third initiation precursor 12
2 may be different from both first initiation precursor 6 and second
3 initiation precursor 8. Alternatively, third initiation precursor 12 may be
4 the same as either the first or second initiation precursors.

5 Another aspect of the invention includes a deposition method
6 comprising contacting a substrate with first initiation precursor 6 and
7 forming a first initiation precursor layer on substrate 4. The first
8 initiation layer is contacted with deposition precursor 10, forming a
9 deposition layer on the first initiation layer. At least the deposition
10 layer is contacted with second initiation precursor 8, different from first
11 initiation precursor 6, forming a second initiation layer over substrate 4.

12 Fig. 5 shows substrate 4 having a first initiation layer derived from
13 first initiation precursor 6 on which a deposition layer is formed from
14 deposition precursor 10. Notably, deposition precursor 10 did not form
15 a deposition layer uniformly across substrate 4 since the initiation layer
16 was not formed uniformly across substrate 4. A second initiation
17 precursor may be used to form a second initiation layer on the
18 deposition layer. The invention thus contemplates using a second
19 initiation precursor different from the first initiation precursor even
20 though the second initiation precursor might not fill openings in the first
21 initiation layer.

22 However, the invention also contemplates that the contacting with
23 the second initiation precursor further comprises contacting a portion of

1 substrate 4 on which the first initiation layer did not form and wherein
2 forming the second initiation layer occurs on at least such portion.
3 Accordingly, forming the second initiation layer could also occur on the
4 portion of substrate 4 on which the first initiation layer did not form as
5 well as on the deposition layer. Fig. 6 shows second initiation precursor
6 8 forming a second initiation layer on the portion of substrate 4 on
7 which the first initiation layer did not form. If second initiation
8 precursor 8 also formed an initiation layer on the deposition layer, then
9 the second initiation layer would exist over the first initiation layer, as
10 well as comprise part of the first initiation layer.

11 In another aspect of the invention, at least the deposition layer of
12 wafer portion 2 shown in Fig. 5 may be contacted with a plurality of
13 initiation precursors. At least one of such plurality may be different
14 from the first initiation precursor and the plurality may form a second
15 initiation layer over the substrate. The contacting with the plurality of
16 initiation precursors may further comprise contacting a portion of the
17 substrate on which the first initiation layer did not form and the
18 formation of the second initiation layer may occur on at least such
19 portion. Also, the contacting with the plurality of initiation precursors
20 may occur simultaneously or separately. Accordingly, one of the plurality
21 of initiation precursors may comprise first initiation precursor 6, yet
22 second initiation precursor 8 may be provided to form an initiation layer
23 on a portion of substrate 4 where the first initiation layer did not form.

1 A variety of particular initiation precursors and deposition
2 precursors may be used in a variety of combinations according to the
3 aspects of the present invention. Trimethyl aluminum (TMA) is one of
4 several possible deposition precursors. TMA may be used beneficially
5 with H_2O , H_2O_2 , CH_3OH , or other alcohols as initiation precursors. In
6 keeping with the above description, selection of particular precursors will
7 depend on the properties of a surface upon which such precursor is to
8 form an initiation or deposition layer. For example, H_2O may be used
9 as a first initiation precursor to chemisorb on a silicon surface to form
10 an initiation layer of -OH groups, producing hydrogen gas (H_2) as a
11 byproduct. This is a self-limiting process, but it is contemplated
12 that -OH groups might not form an initiation layer in select areas.
13 Accordingly, H_2O_2 , CH_3OH , or other alcohols may be used to form an
14 initiation layer also having an -OH termination to which TMA will
15 chemisorb as the deposition precursor.

16 The second initiation precursor different from the first initiation
17 precursor may be contacted with the silicon surface simultaneously with
18 the H_2O , separately from the H_2O , or after formation of the deposition
19 layer. Contacting TMA with the -OH initiation layer will produce CH_4
20 as a byproduct when the hydrogen atoms of the -OH groups chemisorb
21 with one or more methyl groups of the TMA, resulting in aluminum
22 bonding to one or more oxygen atoms on the silicon surface. H_2O may
23 then be contacted with the deposition layer to form a second initiation

1 layer. In the alternative, a third initiation precursor different from
2 either the first or second initiation precursor may contact the deposition
3 layer to form the second initiation layer. The TMA and H₂O (or
4 alternative second initiation precursors) deposition method may be used
5 to form an aluminum oxide (Al₂O₃) film.

6 As shown in Figs. 1-7 and 9, initiation and deposition precursors
7 6, 8, and 10 chemisorb with subsequent precursors to form first initiation
8 compound 16, second initiation compound 18, and deposition compound
9 20, respectively. At least a portion of each precursor thus becomes a
10 part of the final deposited material. For example, with H₂O as an
11 initiation precursor -OH forms on the silicon substrate as first initiation
12 precursor 6 and -O- remains as first initiation compound 16 after
13 chemisorption with a deposition precursor. Similarly, with TMA as a
14 deposition precursor -Al(CH₃)₂ forms on the first initiation layer and
15 remains as -Al- after chemisorption with a subsequent initiation
16 precursor.

17 For an Al₂O₃ deposition from TMA/H₂O, and perhaps other
18 depositions, chamber temperature may be from about 250 to about
19 350 °C, preferably about 300 °C, and chamber pressure may be from
20 about 100 milliTorr to about 10 Torr, preferably about 200 milliTorr.
21 Using a GENUS (TM) ALD tool, deposition of aluminum oxide from
22 TMA and H₂O may be achieved at a rate of about 0.84 Angstroms per
23 cycle. The first step of the cycle may include pulsing about 1 Liter of

1 H₂O at about 20 Torr for from about 200 to about 300 microseconds
2 (μ sec). About 1 Liter of a carrier at about 20 Torr may be pulsed for
3 from about 500 to about 1000 μ sec to purge the H₂O. Next, about 1
4 Liter of TMA at about 20 Torr may be pulsed at for from about 100
5 to about 200 μ sec followed by purging as indicated to complete the
6 cycle. In keeping with the aspects of the present invention described
7 herein, H₂O₂, CH₃OH, or other alcohols may be used in the above
8 method as second initiation precursors to reduce defect formation.

9 Other types of film may be formed using deposition methods as
10 disclosed herein. When SiH₄ or SiCl₄ are to be used as initiation
11 precursors, alternate precursors include chlorosilanes (SiHCl₃, SiH₂Cl₂, and
12 SiH₃Cl) and methysilanes (such as Si(CH₃)_nH_{4-n}, wherein n=1 to 4). It
13 is also contemplated that other alternatives to initiation precursors exist
14 that may be used, depending on the corresponding deposition precursors
15 and surface properties of a substrate.

16 Turning to Fig. 7, a wafer portion 20 is shown having a first
17 substrate region 26 and a second substrate region 28. Each substrate
18 region has a property causing a difference between the susceptibility of
19 the first and second regions to formation of an initiation layer by a first
20 initiation precursor. Accordingly, contacting first region 26 and second
21 region 28 with first initiation precursor 6 forms an initiation layer on
22 first region 26. Contacting at least a part of the substrate, including
23

1 second substrate region 28, with second initiation precursor 8 forms an
2 initiation layer on second region 28.

3 Second substrate region 28 may result from a defect in or
4 contamination of an otherwise homogeneous substrate, causing the
5 difference in susceptibility to formation of an initiation layer by first
6 initiation precursor 6. Such difference may also be the product of two
7 different materials forming each substrate region, such as
8 borophosphosilicate glass (BPSG) and polysilicon. Accordingly, it may
9 even be the case that either the first or second region is insulative and
10 the other is conductive. Accordingly, a first portion of the first
11 initiation layer may form on an insulative portion of a substrate, such
12 as first substrate region 26. A second portion of the first initiation
13 layer may form on a conductive portion of a substrate, such as second
14 substrate region 28.

15 In Fig. 8, a top view of wafer portion 20 of Fig. 7 shows a layer
16 of first initiation precursor 6 that is continuous across the substrate
17 surface and a layer of second initiation precursor 8 that is also
18 continuous across the surface of the substrate. Fig. 8 also shows
19 pinholes 24 in the layer of first initiation precursor 6 wherein no
20 initiation layer was formed. Such pinholes are shown to not be
21 continuous, since at least one pinhole exists that is not connected to a
22 second pinhole by a region wherein no initiation layer was formed.
23

1 According to one aspect of the invention, substantially all of the
2 first portion of the initiation layer may be continuous and at least some
3 of a second portion of the initiation layer is not continuous. Such a
4 result is produced when substantially all of first region 26 is continuous
5 and another region exists wherein pinholes 24 are formed in the
6 initiation layer over second region 28. Such a region may also exist
7 when second region 28 is intentionally not continuous.

8 Another aspect of the invention similarly includes first initiation
9 precursor 6 forming a negligible, if any, amount of an initiation layer on
10 second region 28. In keeping with the present invention, second
11 region 28 may comprise a variety of materials, including those intended
12 to form a designated pattern such as shown in Fig. 8 and different from
13 the material comprising first substrate region 26. The deposition
14 methods of the present invention may be helpful in forming such
15 patterned areas by contacting a first-type surface of a substrate and a
16 second-type surface of a substrate different from the first-type surface
17 with a first initiation precursor and forming a first initiation layer
18 substantially selectively on the first-type surface relative to the second-
19 type surface. The initiation layer may then be contacted with a
20 deposition precursor and a deposition layer formed substantially
21 selectively over the first-type surface relative to the second-type surface.

22 Generally, substantially selective deposition is most desirable when
23 substantially all of the first-type surface is continuous and substantially

1 all of the second-type surface is also continuous. When multiple types
2 of continuous surfaces are provided within a substrate, yet deposition is
3 only desired on one such surface, such a method may be useful.
4 According to the present invention, the first-type surface may even have
5 a common border with the second-type surface. In the various types of
6 arrangements of the first-type and second-type surfaces described above,
7 it is desirable that the first initiation precursor form a negligible, if any,
8 amount of the initiation layer on the second-type surface, surpassing
9 mere substantial selectivity.

10 Turning to Fig. 9, a wafer portion 30 is shown having a recess 34
11 formed therein. Wafer portion 30 further comprises an insulation
12 material 36 and a conductive material 38, formed in recess 34. In this
13 regard, wafer portion 30 could exemplify a wafer portion having a BPSG
14 layer and a container opening formed therein for a container capacitor
15 conductive material 38 may comprise a storage node within the container
16 opening. Such a conductive material may comprise polysilicon. As
17 exemplified by Fig. 9, a first initiation precursor 6 may form an
18 initiation layer on insulative material 36 without forming an initiation
19 layer on conductive material 38, and vice versa. A deposition precursor
20 may then form a deposition layer substantially selectively over insulative
21 material 36. Alternatively, second initiation precursor 8 may form a
22 second portion of the initiation layer on conductive material 38 when
23 such is desired.

1 In compliance with the statute, the invention has been described
2 in language more or less specific as to structural and methodical
3 features. It is to be understood, however, that the invention is not
4 limited to the specific features shown and described, since the means
5 herein disclosed comprise preferred forms of putting the invention into
6 effect. The invention is, therefore, claimed in any of its forms or
7 modifications within the proper scope of the appended claims
8 appropriately interpreted in accordance with the doctrine of equivalents.
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